

RB715F SCHOTTKY BARRIER DIODE

FEATURES:

Power dissipation

$$P_D: \quad 200 \quad \text{mW} \quad (T_{amb}=25^\circ\text{C})$$

Collector current

$$I_F: \quad 30 \quad \text{mA}$$

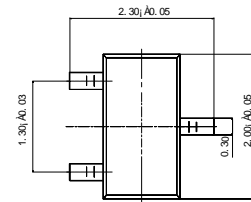
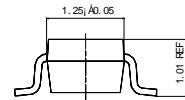
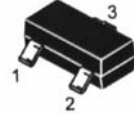
Collector-base voltage

$$V_R: \quad 40 \quad \text{V}$$

Operating and storage junction temperature range

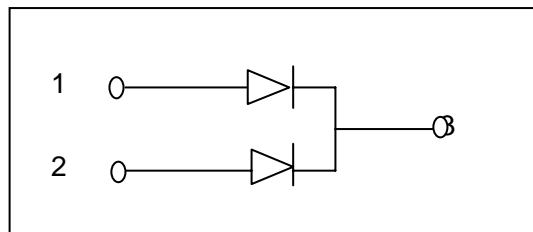
$$T_J, T_{stg}: -55^\circ\text{C} \text{ to } +150^\circ\text{C}$$

SOT-323



Unit: mm

CIRCUIT:



MARKING: 3D

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)}$	$I_R=100\mu\text{A}$	40		V
Reverse voltage leakage current	I_R	$V_R=10\text{V}$		1	μA
Forward voltage	V_F	$I_F=1\text{mA}$		0.37	V
Diode capacitance	C_D	$V_R=1\text{V}, f=1\text{MHz}$		5	pF